

Data Sheet April 1, 2005 FN3146.4

16-Channel/Differential 8-Channel, CMOS High Speed Analog Multiplexer

The HI-516 is a monolithic, dielectrically isolated, highspeed, high-performance CMOS analog multiplexer. It offers unique built-in channel selection decoding plus an inhibit input for disabling all channels. The dual function of address input A₃ enables the HI-516 to be user programmed either as a single ended 16-Channel multiplexer by connecting 'out A' to 'out B' and using A3 as a digital address input, or as an 8-Channel differential multiplexer by connecting A3 to the V- supply. The substrate leakages and parasitic capacitances are reduced substantially by using the Intersil Dielectric Isolation process to achieve optimum performance in both high and low level signal applications. The low output leakage current (I_{D(OFF)} < 100pA at 25^oC) and fast settling (t_{SETTLE} = 800ns to 0.01%) characteristics of the device make it an ideal choice for high speed data acquisition systems, precision instrumentation, and industrial process control.

For MIL-STD-883 compliant parts, request the HI-516/883 data sheet.

Ordering Information

PART NUMBER	TEMP. RANGE (°C)	PACKAGE	PKG. DWG.#
HI3-0516-5	0 to 75	28 Ld PDIP	E28.6
HI3-0516-5Z (See Note)	0 to 75	28 Ld PDIP* (Pb-free)	E28.6

^{*}Pb-free PDIPs can be used for through hole wave solder processing only. They are not intended for use in Reflow solder processing applications.

NOTE: Intersil Pb-free products employ special Pb-free material sets; molding compounds/die attach materials and 100% matte tin plate termination finish, which are RoHS compliant and compatible with both SnPb and Pb-free soldering operations. Intersil Pb-free products are MSL classified at Pb-free peak reflow temperatures that meet or exceed the Pb-free requirements of IPC/JEDEC J STD-020.

Features

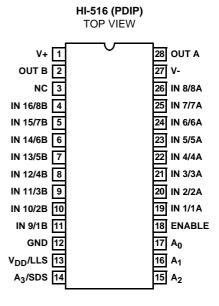
Access Time (Typical)
• Settling Time
• Low Leakage (Typical) - IS(OFF)
Low Capacitance (Max) C _{S(OFF)}
Off Isolation at 500kHz
Low Charge Injection Error
Single Ended to Differential Selectable (SDS)
Logic Level Selectable (LLS)
Die Frank Australia (Dallio Occasiono)

• Pb-Free Available (RoHS Compliant)

Applications

- Data Acquisition Systems
- · Precision Instrumentation
- · Industrial Control

Pinout



Truth Tables

HI-516 USED AS A 16-CHANNEL MULTIPLEXER OR DUAL 8-CHANNEL MULTIPLEXER (NOTE 1)

USE A ₃ AS DIGITAL ADDRESS INPUT				ON CHANNEL TO		
ENABLE	A ₃ A ₂ A ₁ A		A ₀	OUT A	OUT B	
L	Х	Х	Х	Х	None	None
Н	L	L	L	L	1A	None
Н	L	L	L	Н	2A	None
Н	L	L	Н	L	3A	None
Н	L	L	Н	Н	4A	None
Н	L	Н	L	L	5A	None
Н	L	Н	L	Н	6A	None
Н	L	Н	Н	L	7A	None
Н	L	Н	Н	Н	8A	None
Н	Н	L	L	L	None	1B
Н	Н	L	L	Н	None	2B
Н	Н	L	Н	L	None	3B
Н	Н	L	Н	Н	None	4B
Н	Н	Н	L	L	None	5B
Н	Н	Н	L	Н	None	6B
Н	Н	Н	Н	L	None	7B
Н	Н	Н	Н	Н	None	8B

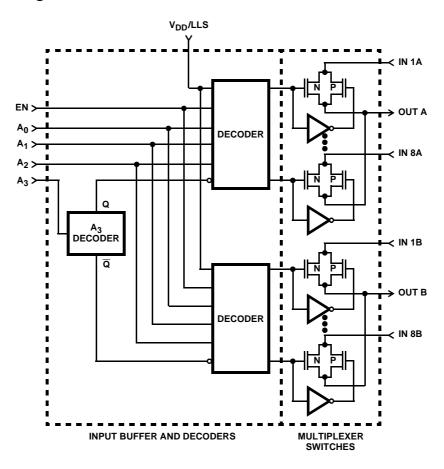
NOTE:

HI-516 USED AS A DIFFERENTIAL 8-CHANNEL MULTIPLEXER

A ₃ CONNECTED TO V- SUPPLY				ON CHANNEL TO		
ENABLE	A ₂	A ₂ A ₁ A ₀		OUT A	OUT B	
L	Х	Х	Х	None	None	
Н	L	L	L	1A	1B	
Н	L	L	Н	2A	2B	
Н	L	Н	L	ЗА	3B	
Н	L	Н	Н	4A	4B	
Н	Н	L	L	5A	5B	
Н	Н	L	Н	6A	6B	
Н	Н	Н	L	7A	7B	
Н	Н	Н	Н	8A	8B	

For 16-channel single-ended function, tie 'out A' to 'out B'; for dual 8-channel function use the A₃ address pin to select between MUX A and MUX B, where MUX A is selected with A₃ low.

Functional Block Diagram



A ₃ DECODE					
A ₃	Q	Q			
Н	Н	L			
L	L	Н			
V-	L	L			

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Absolute Maximum Ratings

V+ to V
(V-) -2V to (V+) +2V
Digital Input Voltage:
TTL Levels Selected (V _{DD} /LLS Pin = GND or Open)
V _{A0-2}
V _{A3/SDS} (V-) -2V to (V+) +2V
CMOS Levels Selected (V _{DD} /LLS Pin = V _{DD})
V _{A0.3} 2V to (V+) +2V

Thermal Information

Thermal Resistance (Typical, Note 2)	θ _{JA} (^o C/W)
PDIP Package*	60
Maximum Junction Temperature	
Plastic Package	150 ^o C
Maximum Storage Temperature Range65	5 ⁰ C to 150 ⁰ C
Maximum Lead Temperature (Soldering 10s)	300°C
*Pb-free PDIPs can be used for through hole wave solde	er processing
only. They are not intended for use in Reflow solder pro	ocessing
applications.	

Operating Conditions

Temperature Ranges	
HI-516-5	0°C to 75°C

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

2. $\theta_{\mbox{\scriptsize JA}}$ is measured with the component mounted on an evaluation PC board in free air.

Electrical Specifications Supplies = +15V, -15V; V_{AH} (Logic Level High) = 2.4V, V_{AL} (Logic Level Low) = 0.8V; V_{DD}/LLS = GND. (Note 3) Unless Otherwise Specified

	TEST CONDITIONS	TEMP (°C)	-5			
PARAMETER			MIN	TYP	MAX	UNITS
DYNAMIC CHARACTERISTICS		<u>'</u>	"			
Access Time, t _A		25	-	130	175	ns
		Full	-	-	225	ns
Break-Before-Make Delay, t _{OPEN}		25	10	20	-	ns
Enable Delay (ON), t _{ON(EN)}		25	-	120	175	ns
Enable Delay (OFF), t _{OFF(EN)}		25	-	140	175	ns
Settling Time	To 0.1%	25	-	250	-	ns
	To 0.01%	25	-	800	-	ns
Charge Injection Error	Note 6	25	-	-	20	mV
Off Isolation	Note 7	25	55	-	-	dB
Channel Input Capacitance, C _{S(OFF)}		25	-	-	10	pF
Channel Output Capacitance, C _{D(OFF)}		25	-	-	25	pF
Digital Input Capacitance, CA		25	-	-	10	pF
Input to Output Capacitance, CDS(OFF)		25	-	0.02	-	pF
DIGITAL INPUT CHARACTERISTICS	·					
Input Low Threshold, V _{AL} (TTL)	Note 3	Full	-	-	0.8	V
Input High Threshold, V _{AH} (TTL)	Note 3	Full	2.4	-	-	V
Input Low Threshold, V _{AL} (CMOS)	Note 3	Full	-	-	0.3V _{DD}	V
Input High Threshold, V _{AH} (CMOS)	Note 3	Full	0.7V _{DD}	-	-	V
Input Leakage Current, I _{AH} (High)		Full	-	-	1	μА

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	TEST	TEMP (°C)	-5			
PARAMETER	CONDITIONS		MIN	TYP	MAX	UNITS
Input Leakage Current, I _{AL} (Low)		Full	-	-	25	μА
ANALOG CHANNEL CHARACTERISTIC	cs	1		1	1	1
Analog Signal Range, V _{IN}	Note 4	Full	-15	-	+15	V
On Resistance, r _{ON}	Note 5	25	-	620	750	Ω
		Full	-	-	1,000	Ω
Off Input Leakage Current, I _{S(OFF)}		25	-	0.01	-	nA
		Full	-	-	50	nA
Off Output Leakage Current, ID(OFF)		25	-	0.03	-	nA
		Full	-	-	100	nA
On Channel Leakage Current, I _{D(ON)}		25	-	0.04	-	nA
POWER SUPPLY CHARACTERISTICS				1	1	
Power Dissipation, P _D		Full	-	-	900	mW
I+, Current	V _{EN} = 2.4V	Full	-	-	30	mA
I-, Current		Full	-	-	30	mA

NOTES:

- 3. V_{DD}/LLS pin = open or grounded for TTL compatibility. V_{DD}/LLS pin = V_{DD} for CMOS compatibility.
- 4. At temperatures above 90° C, care must be taken to assure V_{IN} remains at least 1V below the V_{SUPPLY} for proper operation.
- 5. $V_{IN} = \pm 10 V$, $I_{OUT} = -100 \mu A$.
- 6. $V_{IN} = 0V$, $C_L = 100 pF$, enable input pulse = 3V, f = 500 kHz.
- 7. V_{EN} = 0.8V, V_{IN} = $3V_{RMS}$, f = 500kHz, C_L = 40pF, R_L = 1K, Pin 3 grounded.

Test Circuits and Waveforms V_{DD}/LLS = GND, Unless Otherwise Specified.

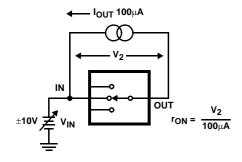


FIGURE 1. ON RESISTANCE TEST CIRCUIT

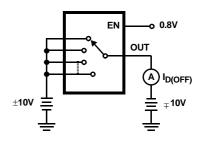


FIGURE 2. I_{D(OFF)} TEST CIRCUIT (NOTE 8)

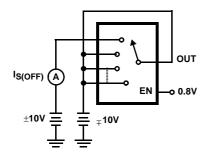


FIGURE 3. I_{S(OFF)} TEST CIRCUIT (NOTE 8)

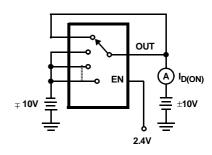


FIGURE 4. I_{D(ON)} TEST CIRCUIT (NOTE 8)

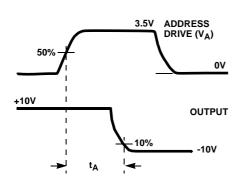


FIGURE 5A. MEASUREMENT POINTS

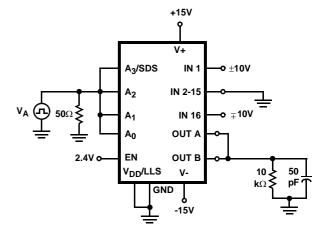


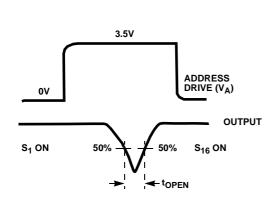
FIGURE 5B. TEST CIRCUIT

NOTE:

8. Two measurements per channel: $\pm 10 \text{V}$ and $\mp 10 \text{V}$. (Two measurements per device for $I_{D(OFF)} \pm 10 \text{V}$ and $\mp 10 \text{V}$).

FIGURE 6. ACCESS TIME

Test Circuits and Waveforms V_{DD}/LLS = GND, Unless Otherwise Specified. (Continued)



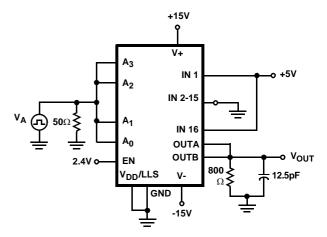
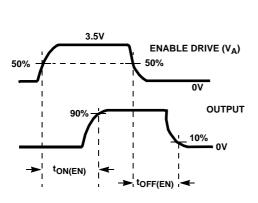


FIGURE 7A. MEASUREMENT POINTS

FIGURE 7B. TEST CIRCUIT

FIGURE 7. BREAK-BEFORE-MAKE DELAY



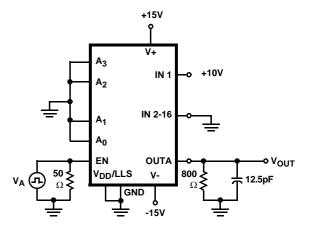
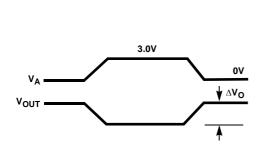


FIGURE 8A. MEASUREMENT POINTS

FIGURE 8B. TEST CIRCUIT

FIGURE 8. ENABLE DELAYS



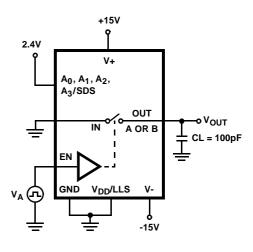


FIGURE 9A. MEASUREMENT POINTS

FIGURE 9B. TEST CIRCUIT

 ΔV_{O} is the measured voltage error due to charge injection. The error in coulombs is Q = C_{L} x ΔV_{O} .

FIGURE 9. CHARGE INJECTION

Die Characteristics

DIE DIMENSIONS:

2250μm x 3720μm x 485μm

METALLIZATION:

Type: CuAl

Thickness: 16kÅ ±2kÅ

PASSIVATION:

Type: Nitride Over Silox Nitride Thickness: 3.5kÅ ±1kÅ Silox Thickness: 12kÅ ±2kÅ

WORST CASE CURRENT DENSITY:

 $1.64 \times 10^5 \text{ A/cm}^2$

Metallization Mask Layout

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ENABLE

V_{DD}/LLS GND (13) (12) A₃/SDS (14) A₀ A₁ A₂ (17) (16) (15) (18)IN 1/1A (19) (10) IN 9/1B (9) IN 10/2B IN 2/2A (20) (8) IN 11/3B IN 3/3A (21) (7) IN 12/4B IN 4/4A (22) (6) IN 13/5B IN 5/5A (23) IN 6/6A (24) (5) IN 14/6B (4) IN 15/7B IN 7/7A (25) (3) IN 16/8B IN 8/8A (26)

(27) (28) (1) (2) $^{+V}$ OUT B All Intersil U.S. products are manufactured, assembled and tested utilizing ISO9000 quality systems. Intersil Corporation's quality certifications can be viewed at www.intersil.com/design/quality

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